

# MPFF100R17RBF 1700V 100A IGBT Module

### **Electrical Features**

- Trench/Fieldstop IGBT
- Half-bridge
- Standard package
- Including anti-parallel FRD



# **Typical Applications**

- High Power Converters
- UPS Systems
- Welding Machine

Maximu	m Rated Values						
Symbol	Item	Conditions			Rating		Unit
IGBT		·					
V <sub>CES</sub>	Collector-emitter voltage	T <sub>vj</sub> =25°C	T <sub>vj</sub> =25°C			1700	
V <sub>GES</sub>	Gate-emitter voltage	-			±20		V
Ic	Collector current,DC	T <sub>C</sub> =100°C,T <sub>vj</sub> =175°	°C		100		Α
I <sub>CRM</sub>	Repetitive peak collector current	t <sub>p</sub> =1ms	t <sub>p</sub> =1ms			200	
P <sub>tot</sub>	Total power dissipation	$T_{C}=25^{\circ}C, T_{vj}=175^{\circ}C$					W
Characte	eristics Values						
Symbol	Item	Conditions			Values		Unit
IGBT				Min.	Тур.	Max.	
I <sub>CES</sub>	Collector-emitter cut-off current	V <sub>CE</sub> =1700V,V <sub>GE</sub> =0V,T <sub>vj</sub> =25°C		-	-	1	mA
I <sub>GES</sub>	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$ -		-	-	250	nA
$V_{\text{GE(th)}}$	Gate-emitter threshold voltage	$I_C=3mA, V_{CE}=V_{GE}, T_{vj}=25^{\circ}C$		5.2	5.92	6.4	
	Collector-emitter saturation voltage	I <sub>C</sub> =100A V <sub>GE</sub> =15V	T <sub>vj</sub> =25°C	-	2.2	2.5	v
V <sub>CEsat</sub>			T <sub>vj</sub> =125°C	-	2.7	-	
			T <sub>vj</sub> =150°C	-		-	
Cies	Input capacitance	$V_{CE}=25V, V_{GE}=0V$ f=1MHz, T <sub>vj</sub> =25°C		-	8.63	-	"Г
Cres	Reverse transfer capacitance			-	0.50	-	nF
Q <sub>G</sub>	Gate charge	V <sub>GE</sub> =-15V+15V		-	0.94	-	uC

# IGBT, Inverter

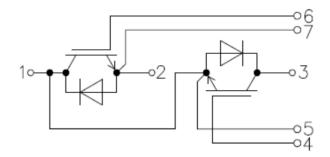
			1	r	r	[	1
			T <sub>vj</sub> =25°C	-	126	-	
t <sub>d(on)</sub>	Turn-on delay time		T <sub>vj</sub> =125°C	-	149	-	-
			T <sub>vj</sub> =150°C	-		-	
			T <sub>vj</sub> =25°C	-	85	-	
t <sub>r</sub>	Rise time	V 000V	T <sub>vj</sub> =125°C	-	93	-	ns
		$V_{\rm CC}=900V,$	$T_{vj}$ =150°C	-		-	
		$I_{C}=100A,$ $V_{GE}=\pm 15V,$	T <sub>vj</sub> =25°C	-	208	-	
$t_{d(off)}$	Turn-off delay time		T <sub>vj</sub> =125°C	-	293	-	
		$R_{G(on)}=2.4 \Omega$ ,	T <sub>vj</sub> =150°C	-		-	
		$= R_{G(off)} = 2.4 \Omega,$	T <sub>vj</sub> =25°C	-	436	-	
$t_{\rm f}$	Fall time	$di/dt=873A/\mu s$	T <sub>vj</sub> =125°C	-	600	-	- - - mJ
		$(T_{vj}=125^{\circ}C)$	T <sub>vj</sub> =150°C	-		-	
		– du/dt=4301V/μs (T <sub>vj</sub> =125°C)	T <sub>vj</sub> =25°C	-	22.5	-	
Eon	Turn-on energy (per pulse)		T <sub>vj</sub> =125°C	-	34.4	-	
			T <sub>vj</sub> =150°C	-		-	
	Turn-off energy (per pulse)		T <sub>vj</sub> =25°C	-	21.9	-	
E <sub>off</sub>			T <sub>vj</sub> =125°C	-	28.1	-	
			T <sub>vj</sub> =150°C	-		-	
R <sub>thJC</sub>	Thermal resistance, junction to case	per IGBT		-		-	K/W
$R_{thCH}$	Thermalresistance, case to heatsink		per IGBT/ $\lambda$ grease=1W/(m·K) -			-	K/W
$T_{vjop}$	Temperature under switching conditions			-40		150	°C
Diada							
Diode, Maximu	inverter						
Symbol	Item	Ca	nditions		Pot	ina	Unit
•	Repetitive peak reverse voltage	Conditions Rating			-	V	
V <sub>RRM</sub>	Forward current,DC	5	$T_{vj}=25^{\circ}C$			1700 100	
I <sub>F</sub>		$T_{\rm C}=100^{\circ}{\rm C}, T_{\rm vj}=175^{\circ}{\rm C}$			200		A
I <sub>FRM</sub>	Repetitive peak forward current	t <sub>p</sub> =1ms			20	00	Α
Charact	eristic Values		T 2500		1.00	2.5	
<b>T</b> 7	Continuous forward voltage	I <sub>F</sub> =100A	$T_{vj}=25^{\circ}C$	-	1.96	2.5	
$V_{\rm F}$		V <sub>GE</sub> =0V	$T_{vj}=125^{\circ}C$	-	1.73	-	V
			T <sub>vj</sub> =150°C	-	102	-	
_			T <sub>vj</sub> =25°C	-	103	-	
I <sub>RM</sub>	Peak reverse recovery current		T <sub>vj</sub> =125°C	-	133	-	A
		- V <sub>R</sub> =900V	T <sub>vj</sub> =150°C	-		-	
	Reverse recovery time	$I_{\rm F}=100{\rm A}$ -di <sub>F</sub> /dt=2736A/µs	T <sub>vj</sub> =25°C	-	123	-	-
t <sub>rr</sub>			T <sub>vj</sub> =125°C	-	578	-	ns
		$(T_{vj}=125^{\circ}C)$	T <sub>vj</sub> =150°C	-		-	
		× ·j/	T <sub>vj</sub> =25°C	-	15.4	-	4
Qr							μC
$Q_{r}$	Recovered charge		$T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	-	31.7	-	μC

			T <sub>vj</sub> =25°C	-	9.0	-	
Erec	Reverse recovery energy		T <sub>vj</sub> =125°C	-	17.9	-	mJ
			T <sub>vj</sub> =150°C	-		-	
R <sub>thJC</sub>	Thermal resistance, junction to case	per diode		-		-	K/W
$R_{thCH}$	Thermalresistance, case to heatsink	per diode/ $\lambda$ grease=1W/(m·K)		-		-	K/W
T <sub>vjop</sub>	Temperature under switching conditions			-40		150	°C

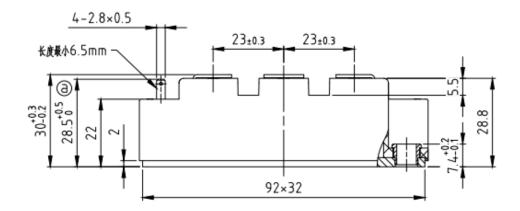
#### Module

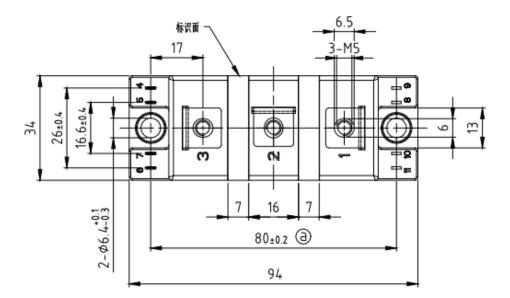
Symbol	Item	Conditions Rating			Unit	
V <sub>ISOL</sub>	Isolation voltage	Terminals to baseplate, RMS,f=50Hz,t=1min	4000		V	
-	Material of module baseplate	-	Cu		-	
-	Internal isolation	Basic insulation(class 1, IEC 61140)	Al <sub>2</sub> O <sub>3</sub>		-	
T <sub>stg</sub>	Storage temperature	-	-40~125		5	°C
Symbol	Item		Values			Unit
		Conditions	Min.	Тур.	Max.	
М	Mounting torque for module mounting	Screw M6	3.0	-	5.0	Nm
	Terminal connection torque	Screw M5	2.5	-	5.0	Nm
$d_{\text{Creep}}$	Creepage distance	Terminal to terminal	-	23	-	
		Terminal to base plate	-	29	-	mm
$d_{\mathrm{Clear}}$	Clearance	Terminal to terminal	-	11	-	
		Terminal to base plate	-	23	-	mm
m	Weight	-	-	150	-	g

### Circuit diagram headline



### Package outlines (Unit: mm)





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1	2023.9.4	初版规格书发布,版本为V1.0	2023 9	Ver1.0   梁华文